



芯基科技

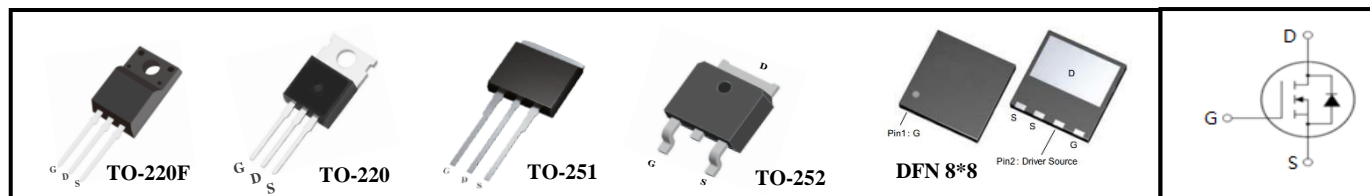
MPSA65M650,MPSP65M650,MPSU65M650, MPSD65M650,MPSY65M650

FEATURES

- $BV_{DSS}=650V, I_D=8A$
- $R_{DS(on)}:0.65\Omega(\text{Max})@V_{GS}=10V$
- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Ordering code	Package	Marking
MPSA65M650	TO-220F	MP65M650
MPSP65M650	TO-220	MP65M650
MPSU65M650	TO-251	MP65M650
MPSD65M650	TO-252	MP65M650
MPSY65M650	DFN 8*8	MP65M650

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-220F	TO-220, TO-251, TO-252, DFN 8*8	
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	650		V
Continuous Drain Current	I_D	8		A
Pulsed Drain Current (note1)	I_{DM}	24		A
Gate-Source Voltage	V_{GSS}	± 30		V
Single Pulse Avalanche Energy (note2)	E_{AS}	80		mJ
Avalanche Current (note1)	I_{AR}	2.5		A
Repetitive Avalanche Energy (note1)	E_{AR}	0.3		mJ
MOSFET dv/dt ruggedness, $V_{DS}=0 \dots 400V$	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS}=0 \dots 400V, I_{SD} \leq I_D$	dv/dt	50		V/ns
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	28	64	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-220F	TO-220, TO-251, TO-252, DFN 8*8	
Thermal Resistance, Junction-to-Case	R_{thJC}	4.5	2	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	62	



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MPSA65M650, MPSP65M650, MPSU65M650, MPSD65M650, MPSY65M650

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 0.25mA$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4A$	--	0.57	0.65	Ω
Gate Resistance	R_G	$f = 1.0MHz, \text{open drain}$	--	14	--	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 100V, f = 1.0MHz$	--	458	--	pF
Output Capacitance	C_{oss}		--	18	--	
Reverse Transfer Capacitance	C_{rss}		--	3	--	
Total Gate Charge	Q_g	$V_{DD} = 400V, I_D = 8A, V_{GS} = 10V$	--	13.4	--	nC
Gate-Source Charge	Q_{gs}		--	2.8	--	
Gate-Drain Charge	Q_{gd}		--	4	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 8A, V_{GS} = 10V, R_G = 25\Omega$	--	38	--	ns
Turn-on Rise Time	t_r		--	20	--	
Turn-off Delay Time	$t_{d(off)}$		--	100	--	
Turn-off Fall Time	t_f		--	20	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	8	A
Pulsed Diode Forward Current	I_{SM}		--	--	24	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 8A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_F = 8A, di_F/dt = 100A/\mu s$	--	314	--	ns
Reverse Recovery Charge	Q_{rr}		--	3	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	19	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 2.5A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$

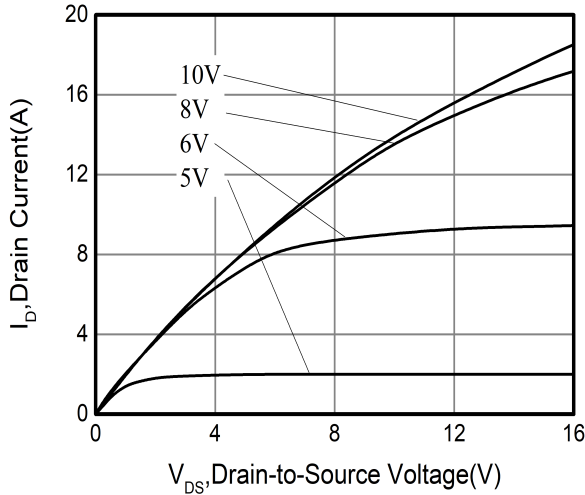


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MPSA65M650, MPSP65M650, MPSU65M650, MPD65M650, MPSY65M650

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)



2. Transfer Characteristics

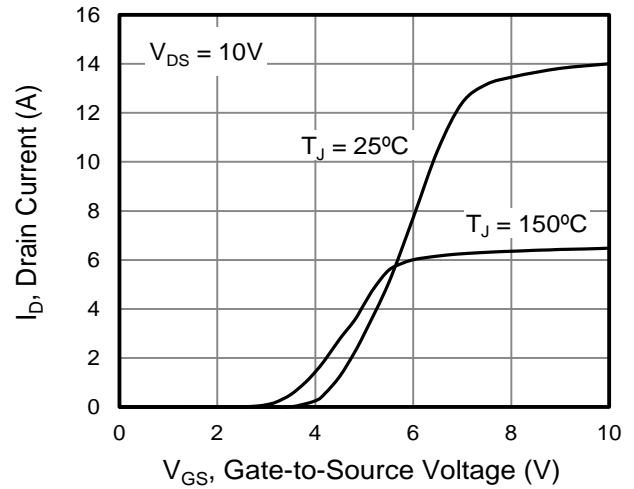


Figure 3. On-Resistance vs Drain Current

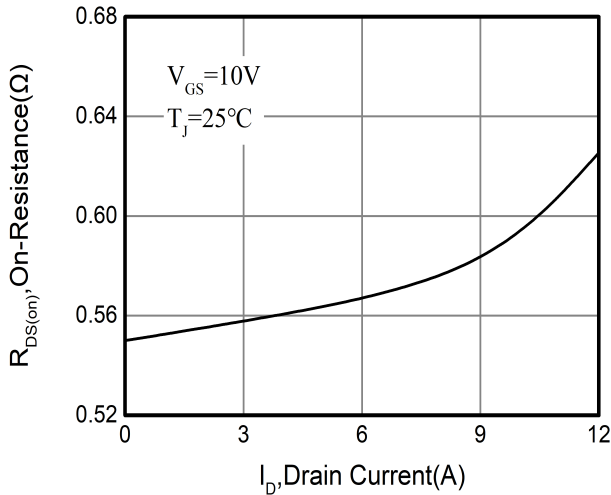


Figure 4. Capacitance

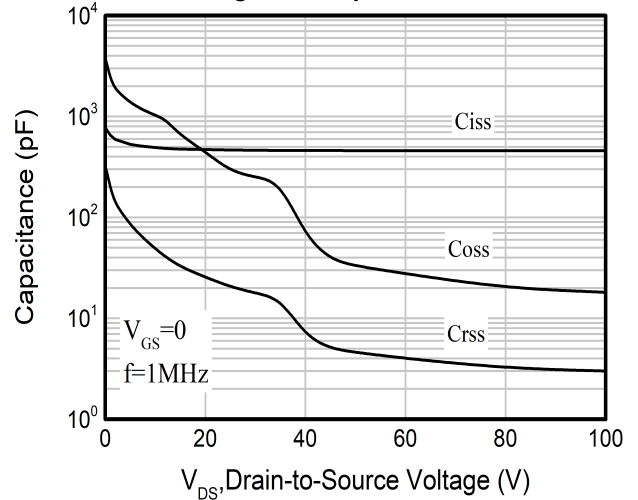


Figure 5. Gate Charge

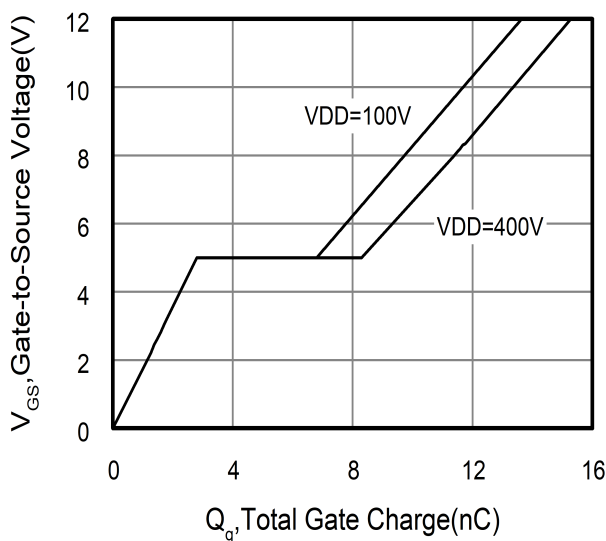
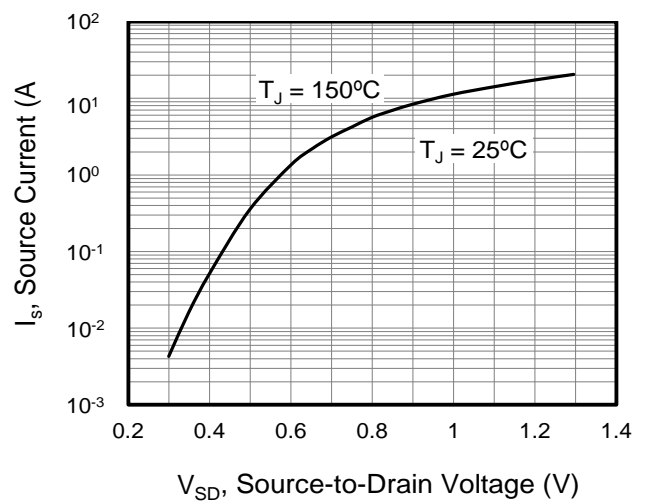


Figure 6. Body Diode Forward Voltage



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

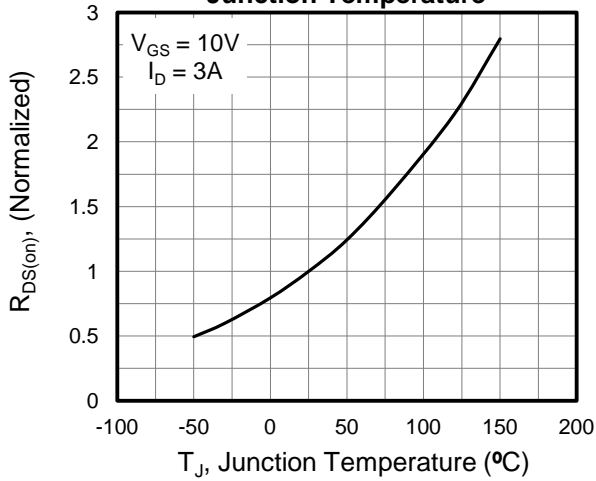


Figure 8. Threshold Voltage vs. Junction Temperature

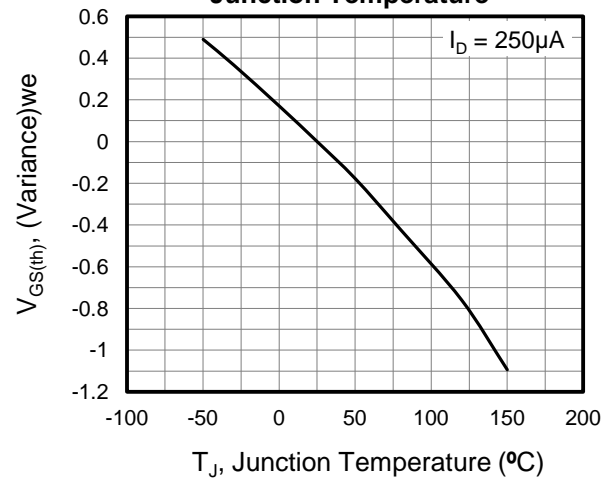


Figure 9. Transient Thermal Impedance TO-220/TO-251/TO-252/DFN 8*8

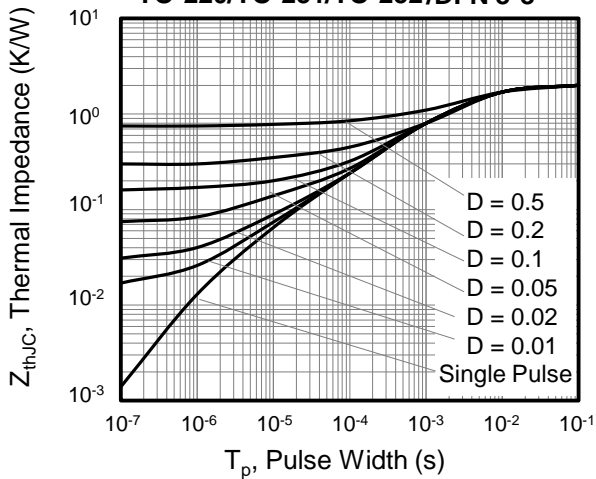


Figure 10. Transient Thermal Impedance TO-220F

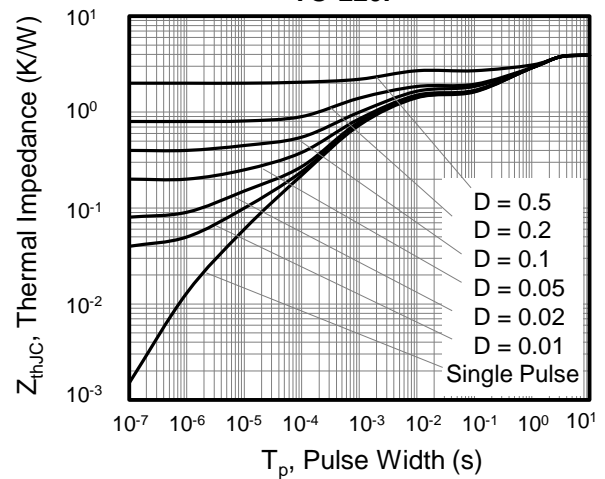


Figure A: Gate Charge Test Circuit and Waveform

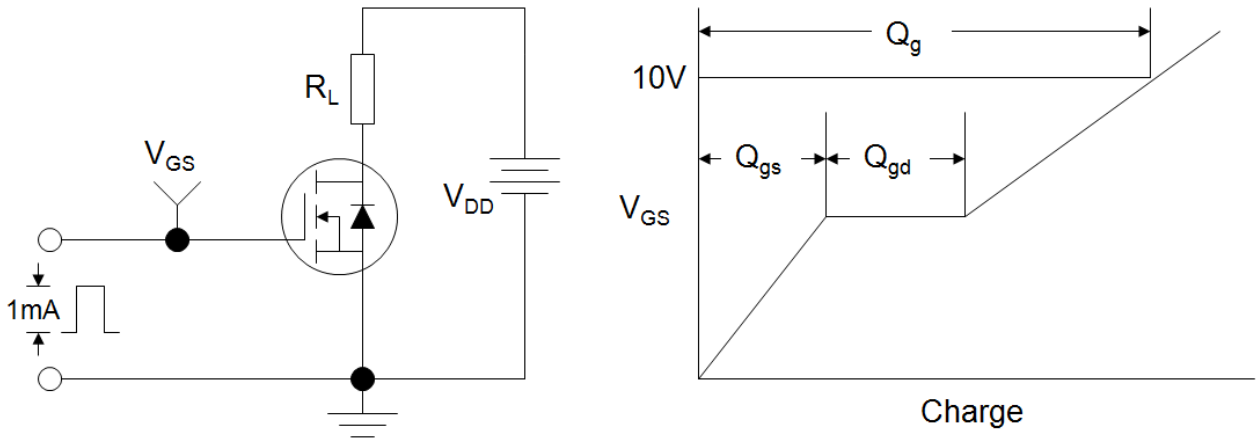


Figure B: Resistive Switching Test Circuit and Waveform

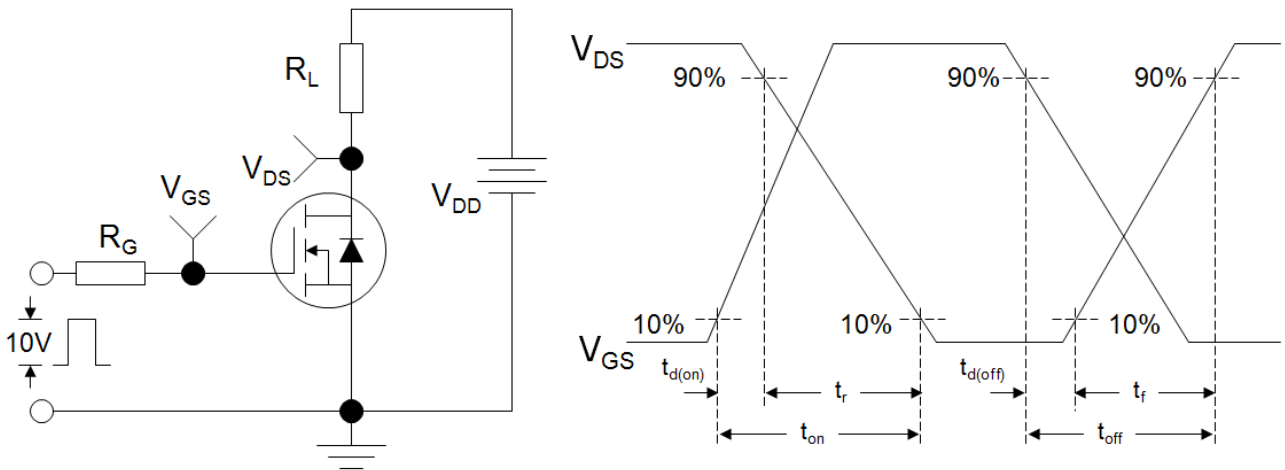
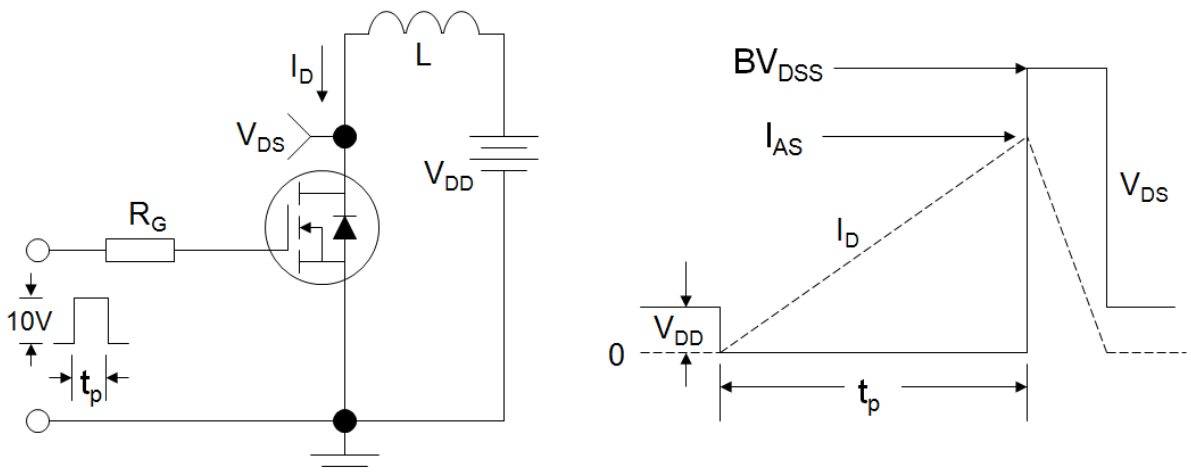
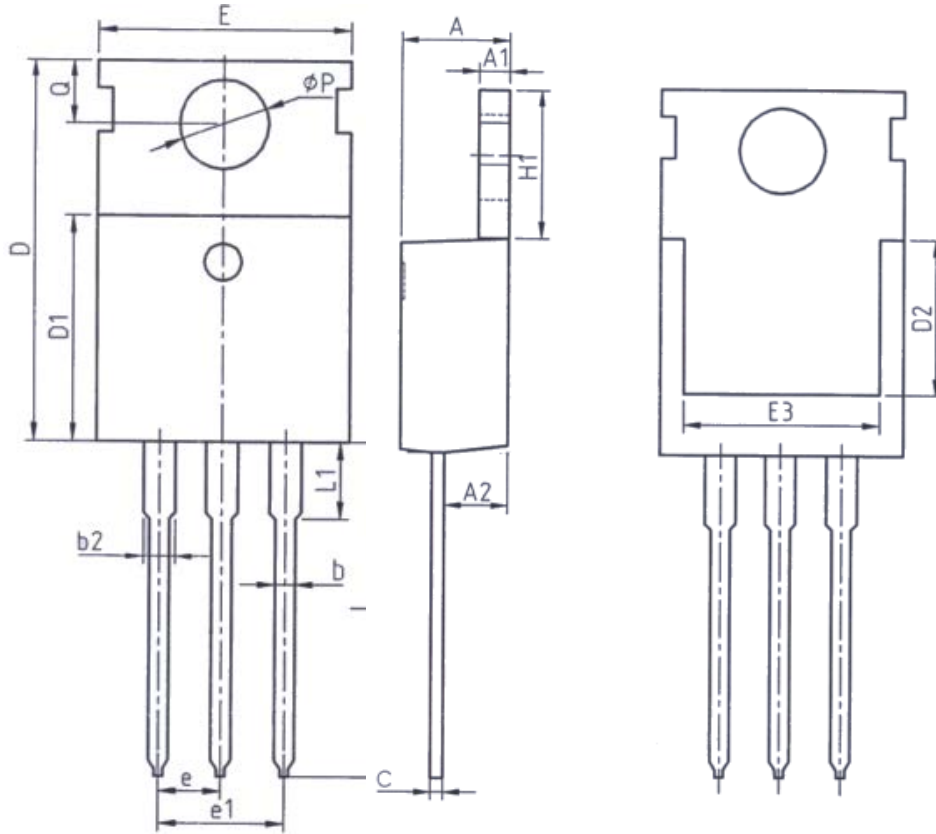


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



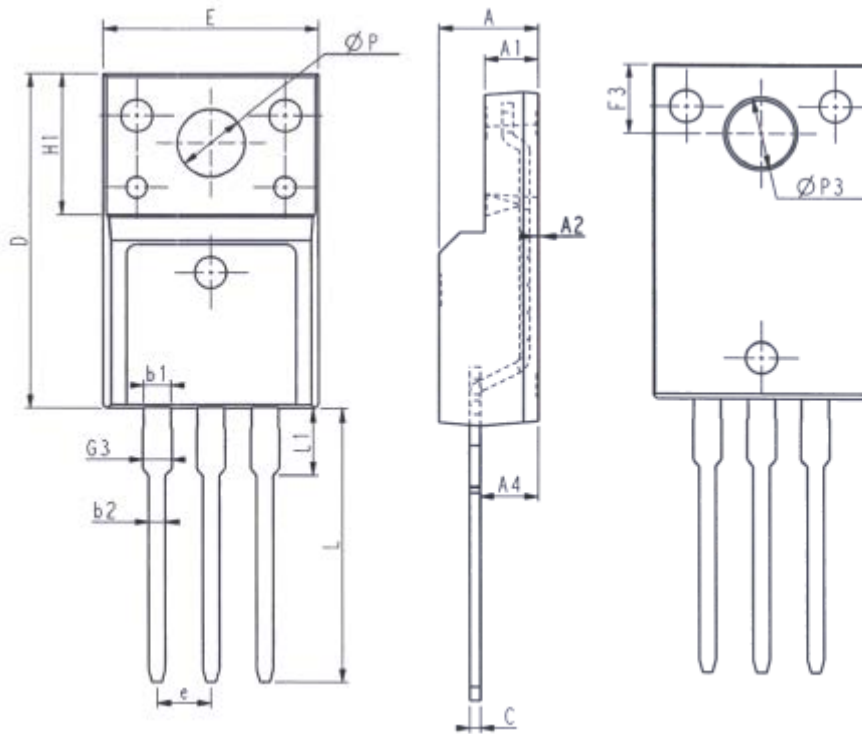
TO-220



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	-

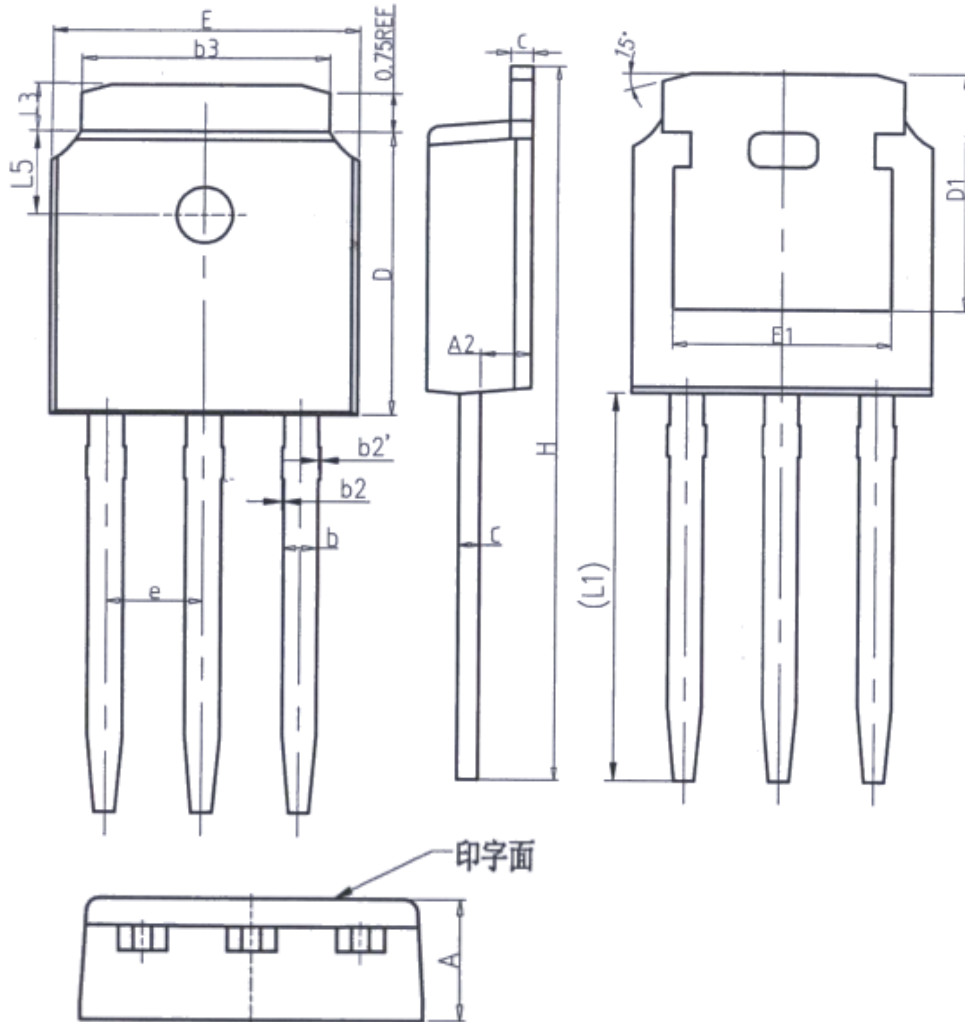
Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	-
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	-	3.40
P	3.40	3.80
Q	2.60	3.00

TO-220F



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13.28
A	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	P	3.03	3.38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
c	0.40	0.65	G3	1.25	1.55
D	15.57	16.17	b1	1.18	1.43
H1	6.70REF		b2	0.70	0.95
e	2.54BSC				

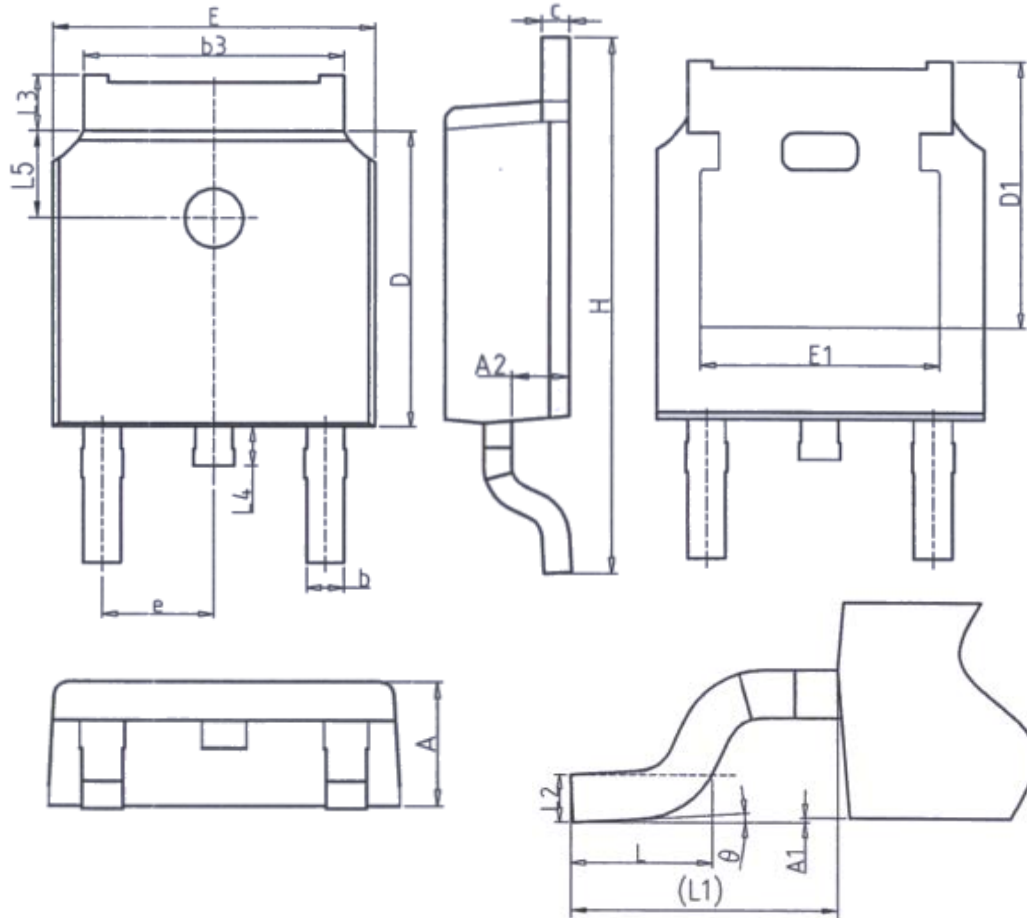
TO-251



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95

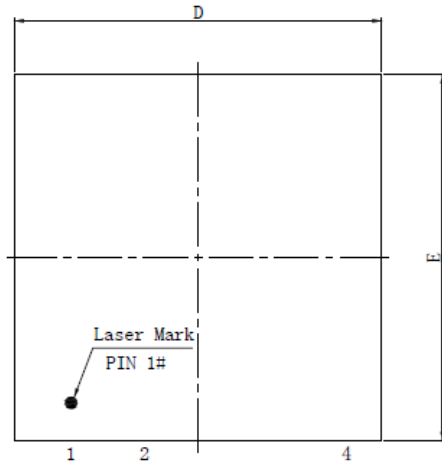
TO-252



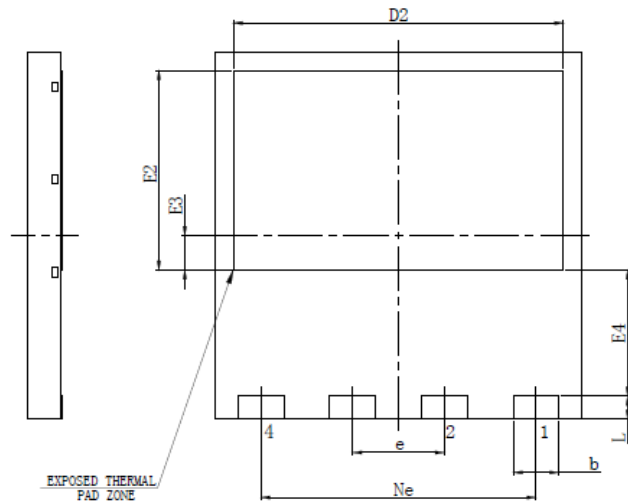
Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
θ	0°	8°

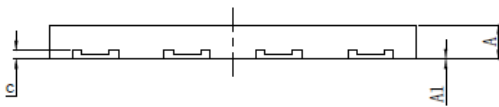
DFN 8x8



TOP VIEW



BOTTOM VIEW



SIDE VIEW

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0	0.02	0.05
b	0.95	1.00	1.05
c	0.18	0.20	0.25
D	7.90	8.00	8.10
Ne	6.00BSC		
e	2.00BSC		
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E2	4.25	4.35	4.45
E3	0.75REF		
E4	2.75REF		
L	0.45	0.50	0.55
载体尺寸	7.60*5.15		